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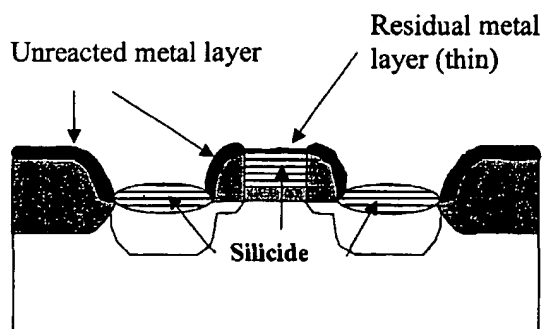
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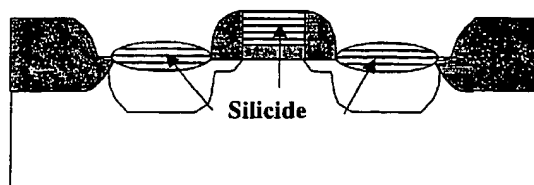
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(54) Title: **GATE ELECTRODES AND THE FORMATION THEREOF**



(3) After silicide formation

(57) Abstract: A method of fabricating a gate electrode for a semiconductor comprising the steps of: providing a substrate; providing on the substrate a layer of a first material of thickness t_p , the first material being selected from the group consisting of Si, Si 1-x-Ge alloy, Ge and mixtures thereof and a layer of metal of thickness t_m ; and annealing the layers, such that substantially all of the first material and the metal are consumed during reaction with one another. [Figure 1]



(4) After metal etch-off



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